TOSHIBA Field Effect Transistor Silicon N Channel MOS Type (L²-π-MOSV)

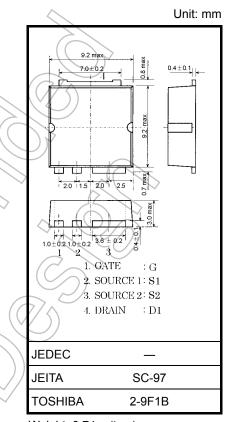
2SK3387

Switching Regulator, DC-DC Converter and Motor Drive Applications

- 4-V gate drive
- Low drain-source ON resistance: R_{DS} (ON) = 0.08 Ω (typ.)
- High forward transfer admittance: $|Y_{fs}| = 17 \text{ S} (typ.)$
- Low leakage current: $I_{DSS} = 100 \ \mu A (V_{DS} = 150 \ V)$
- Enhancement mode: $V_{th} = 0.8 \sim 2.0 \text{ V} (V_{DS} = 10 \text{ V}, I_D = 1 \text{ mA})$

Absolute Maximum Ratings (Ta = 25°C)

Characteristics		Symbol	Rating	Unit	\supset
Drain-source voltage		V _{DSS}	150	V	
Drain-gate voltage ($R_{GS} = 20 \text{ k}\Omega$)		V _{DGR}	150	V	
Gate-source voltage	_	V _{GSS}	±20	V	
Drain current	DC (Note 1)	I _D	18	Ā	
Drain current	Pulse (Note 1)	I _{DP}	54	~	(
Drain power dissipation (Tc = 25° C)		PD	100	W	
Single pulse avalanche energy (Note 2)		Eas	176	mJ	
Avalanche current		I _{AR}	18	A	
Repetitive avalanche energy (Note 3)		EAR	10	mJ	V
Channel temperature		(T _{ch}	150	°C	
Storage temperature range		T _{stg}	-55~150)°C	



Weight: 0.74 g (typ.)

Note: Using continuously under heavy loads (e.g. the application of high temperature/current/voltage and the significant change in temperature, etc.) may cause this product to decrease in the reliability significantly even if the operating conditions (i.e. operating temperature/current/voltage, etc.) are within the absolute maximum ratings. Please design the appropriate reliability upon reviewing the Toshiba Semiconductor Reliability Handbook ("Handling Precautions"/Derating Concept and Methods) and individual reliability data (i.e. reliability test report and estimated failure rate, etc).

Thermal Characteristics

Characteristics	Symbol	Max	Unit
Thermal resistance, channel to case	Rth (ch-c)	1.25	°C/W

Note 1: Ensure that the channel temperature does not exceed 150°C.

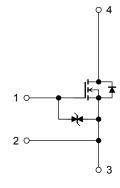
Note 2: V_{DD} = 50 V, T_{ch} = 25°C (initial), L = 800 μ H, R_G = 25 Ω , I_{AR} = 18 A

Note 3: Repetitive rating: pulse width limited by max junction temperature

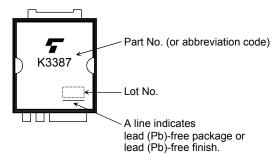
This transistor is an electrostatic-sensitive device. Please handle with caution.

Notice:

Please use the S1 pin for gate input signal return. Make sure that the main current flows into S2 pin.



Marking



Electrical Characteristics (Note 4) (Ta = 25°C)

Chara	cteristics	Symbol	Test Condition	Min	Тур.	Max	Unit
Gate leakage curr	ent	I _{GSS}	$V_{GS} = \pm 16 \text{ V}, \text{ V}_{DS} = 0 \text{ V}$	_	\square	±10	μA
Drain cut-off curre	nt	I _{DSS}	$V_{DS} = 150 \text{ V}, \text{ V}_{GS} = 0 \text{ V}$	_	47	100	μA
Drain-source brea	kdown voltage	V (BR) DSS	$I_{D} = 10 \text{ mA}, V_{GS} = 0 \text{ V}$	150	5-1	> -	V
Gate threshold vo	Itage	V _{th}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 1 \text{ mA}$	0.8) HA	2.0	V
Drain-source ON	resistance	R _{DS (ON)}	$V_{GS} = 4 V, I_D = 9 A$		0.09	0.18	Ω
E			$V_{GS} = 10 V, I_D = 9 A$		0.08	0.12	0
Forward transfer a	admittance	Y _{fs}	$V_{DS} = 10 \text{ V}, \text{ I}_{D} = 9 \text{ A}$)	17		S
Input capacitance		C _{iss}		\leq	1380	_	
Reverse transfer of	capacitance	C _{rss}	$V_{DS} = 10 V, V_{GS} = 0 V, f = 1 MHz$) —	200		pF
Output capacitanc	e	C _{oss}			610		
	Rise time	tr		_	12		
Switching time	Turn-on time	ton		_	20		ns
	Fall time	t	S ₁₀ S ₁₀ S ₂₀		12		115
	Turn-off time	toff	∠		68		
Total gate charge gate-drain)	(gate-source plus	Qg		_	57	_	nC
Gate-source char	ge	Qgs	V _{DD} = 120 V, V _{GS} = 10 V, I _D = 18 A		43	_	nC
Gate-drain ("miller	") charge	Q _{gd}		_	14	_	nC

Note 4: Connect the S1 and S2 pins together, and ground them except during switching time measurement.

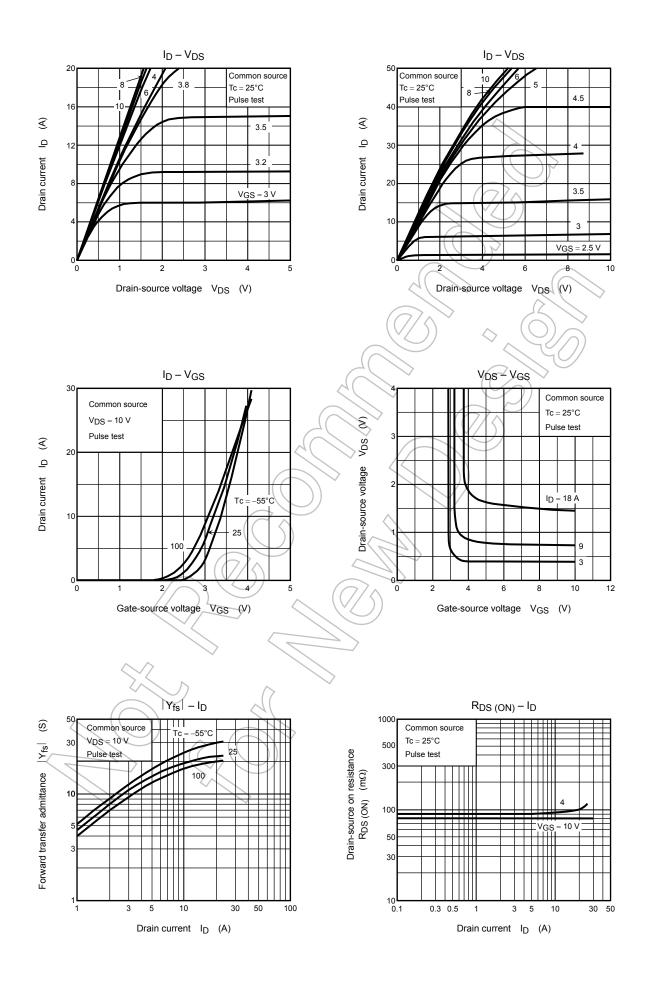
Source-Drain Diode Ratings and Characteristics (Note 5) (Ta = 25°C)

Characteristics	2 C	Symbol	Test Condition	Min	Тур.	Max	Unit
Continuous drain reverse current	(Note 1, 5)	I _{DR} 1	—	—	—	18	А
Pulse drain reverse current	(Note 1, 5)	I _{DRP} 1	—	_	_	54	А
Continuous drain reverse current	(Note 1, 5)	I _{DR} 2	—	_	_	1	А
Pulse drain reverse current	(Note 1, 5)	I _{DRP} 2	—	_	_	4	А
Diode forward voltage		V _{DS2F}	I _{DR1} = 18 A, V _{GS} = 0 V	_	_	-1.7	V
Reverse recovery time		t _{rr}	I _{DR} = 18 A, V _{GS} = 0 V,	_	185	_	ns
Reverse recovery charge		Q _{rr}	dI _{DR} /dt = 100 A/µs		1.3		μC

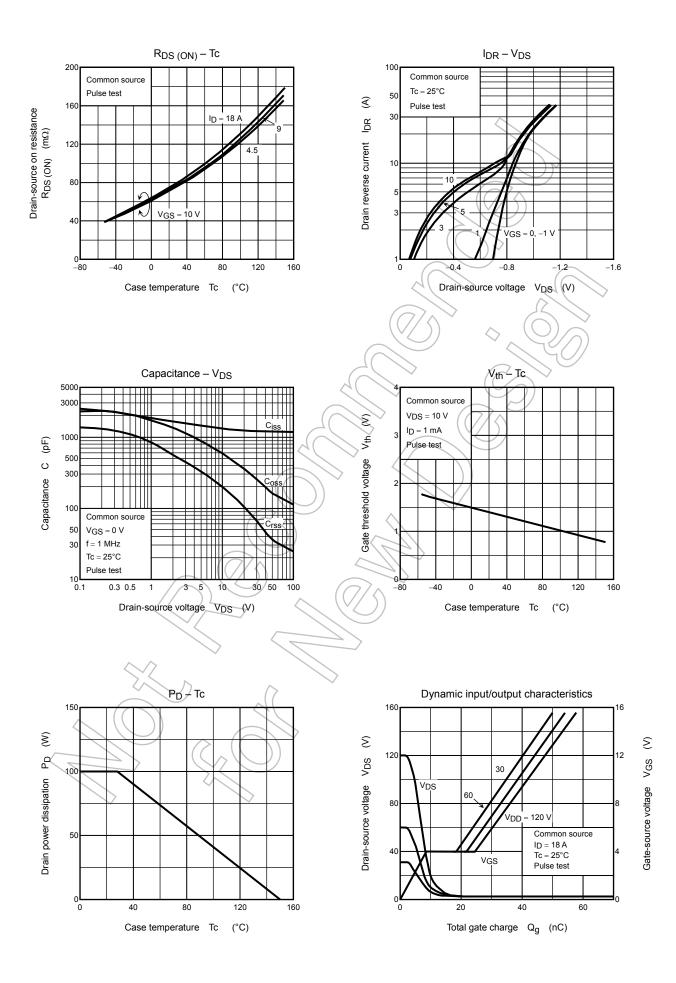
Note 5: I_{DR}1, I_{DRP}1:Current flowing between the drain and the S2 pin. Ensure that the S1 pin is left open. I_{DR}2, I_{DRP}2:Current flowing between the drain and the S1 pin. Ensure that the S2 pin is left open.

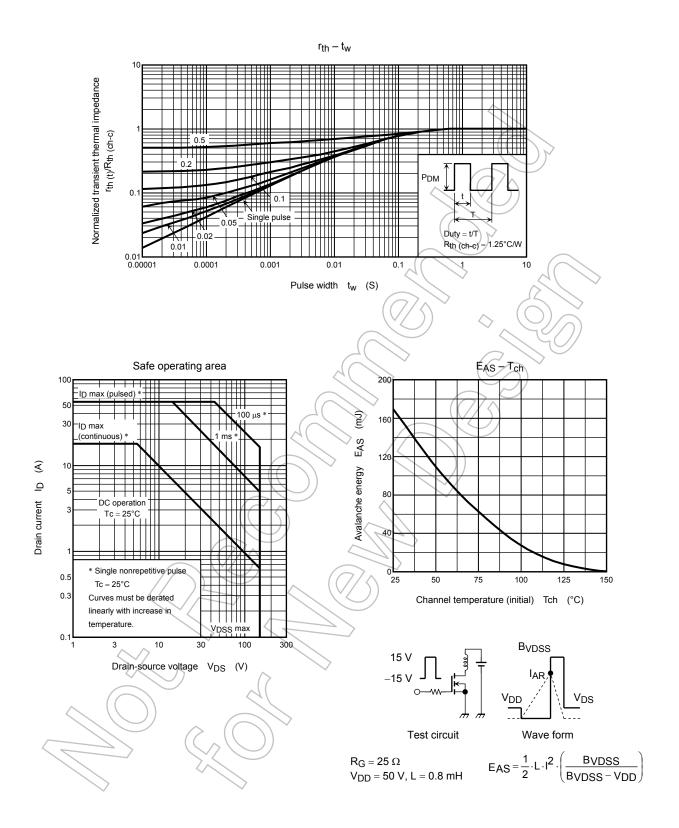
Unless otherwise specified, connect the S1 and S2 pins together, and ground them

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